CNB2301 (ON2270)

Reflective Photosensor

For contactless SW and object detection

Overview

CNB2301 is a small, thin reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity darlington phototransistor used as the photo detector in a single resin package.

■ Features

- Ultraminiature: 2.7 mm × 3.4 mm
- Visible light cutoff resin is used
- High current transfer ratio

■ Applications

- Detection of paper, film and cloth
- Detection of position and edge
- Liquid level sensor
- Detection of rotary positioning
- Start, end mark detection of magnetic tape

■ Absolute Maximum Ratings $T_a = 25$ °C

F	Parameter	Symbol	Rating	Unit	
	Power dissipation	P_{D}	75	mW	
Input (Light emitting diode)	Forward current	I_{F}	50	mA	
	Reverse voltage	V _R	3	V V	
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	20		
	Emitter-collector voltage (Base open)	V_{ECO}	10.29/10.	or V	
	Collector current	I_{C}	30	mA	
	Collector power dissipation	P _C	75	mW	
	Total power dissipation	P _T	100	mW	
Operating ambient temp	T _{opr}	-25 to +85	°C		
Storage temperature	T _{stg}	-30 to +100	°C		

CNB2301

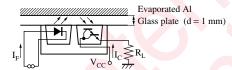
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\blacksquare Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$		0.01	10	μΑ
	Forward voltage	V _F	$I_F = 50 \text{ mA}$		1.3	1.5	V
	Terminal capacitance	C_{T}	$V_R = 0 V, f = 1 MHz$		30		pF
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}$			1.0	μА
Transfer characteristics	Collector current *1, *2	I_{C}	$V_{CC} = 5 \text{ V}, I_F = 2 \text{ mA},$ $R_L = 100 \Omega, d = 1 \text{ mm}$	0.46		12.0	mA
	Drain current	I_D	$V_{CC} = 5 \text{ V}, I_F = 2 \text{ mA},$ $R_L = 100 \Omega$			2.0	μΑ
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 5 \text{ mA}, I_C = 0.5 \text{ mA}$			1.5	V
	Rise time	t _r	$V_{CC} = 10 \text{ V}, I_C = 1 \text{ mA}, R_L =$		150	· ·	μs
	Fall time	t_{f}	100 Ω		150		μs

Note) 1. Input and output are practiced by electricity.

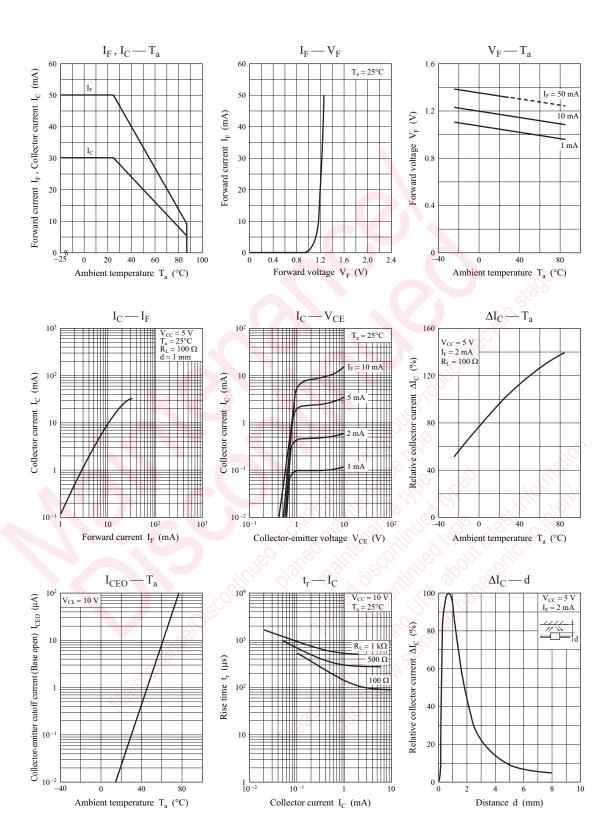
- 2. This device is designed by disregarding radiation.
- 3. *1: Output current measurement circuit



*2: Rank classification

Rank	Q	R	S
I _C (mA)	0.46 to 1.75	1.30 to 4.95	3.15 to 12.0
Color	Pink	Black	Blue

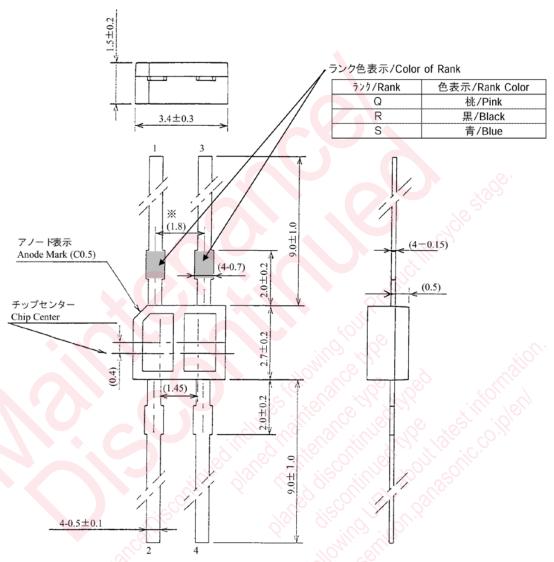
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■ Package (Unit: mm)

LSMFRN4S0001



(注 1) ※リード根元寸法とします。

(Note1) *Indicates root dimensions of lead.

(注 2) ランク色表示は、目視又は顕微鏡に於いて解読できる事。

(Note2) What rank color a sees an attention and can decode in a microscope.

- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Emitter
 - 4: Collector

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